Red Laser Diode



DL-3148-033

Index Guided AlGaInP Laser Diode

Overview

The DL-3148-033 is index guided 635 nm (Typ.) AlGaInP laser diode with low threshold current and high operating temperature. The low threshold current and short wavelength are achieved by a strained multiple quantum well active layer. The lasing wavelength is 635nm which is 8 times brighter than that of 670nm lasers. The DL-3148-033 is suitable for applications such as bar-code scanners, laser printer, and other optical information systems.

Features

•Short wavelength : 635 nm (Typ.) •Low threshold current : Ith = 40 mA (Typ.) •High operating temperature : 5 mW at 50°C •Small package : 5.6 mmØ

Absolute Maximum Ratings at Tc=25°C

Parameter		Symbol	Ratings	Unit	
Light Output		Ро	5	mW	
Reverse Voltage	Laser PIN	VR	2 30	V	
Operating Temperature		Topr	-10 to +50	°C	
Storage Temperature		Tstg	-40 to +85	°C	

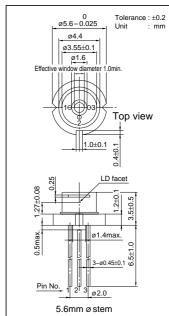
Electrical and Optical Characteristics at Tc=25°C

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Para	meter	Symbol	Condition	Min.	Тур.	Max.	Unit
Threshol	d Current	Ith	CW	-	40	60	mA
Operating	g Current	Iop	Po=5mW	-	55	75	mA
Operatin	g Voltage	Vop	Po=5mW	-	2.2	2.4	V
Lasing W	avelength	λ p	Po=5mW	-	635	640	nm
Beam **)	Perpendicular	heta ot	Po=5mW	25	35	40	deg.
Divergence	Parallel	heta //	Po=5mW	6	8	10	deg.
Off Axis	Perpendicular	$\Delta heta \perp$	-	-	-	±3	deg.
Angle	Parallel	$\Delta heta$ //	-	-	-	±3	deg.
Differentia	l Efficiency	dPo/dIop	-	-	0.4	-	mW/mA
Monitoring C	utput Current	Im	Po=5mW	0.1	0.2	0.5	mA
Astigmatism		As	Po=5mW	-	8	-	μm

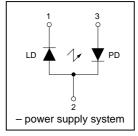
*) Full angle at half maximum note : The above product specifications are subject to change without notice.

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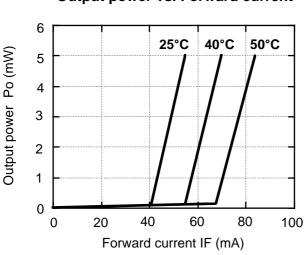
Package Dimensions



Electrical Connection

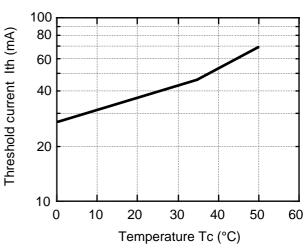


Characteristics

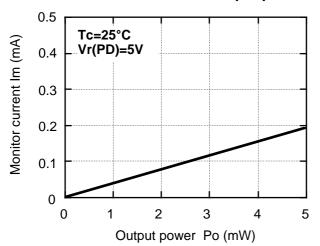


Output power vs. Forward current Threshold

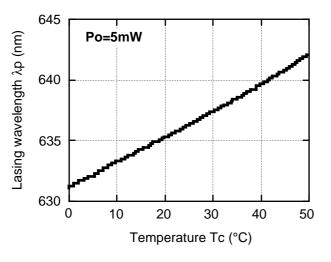
Threshold current vs. Temperature



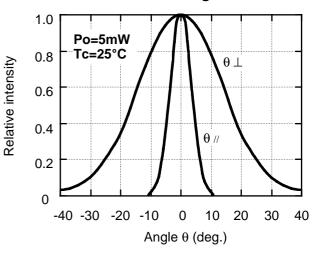
Monitor current vs. Output power



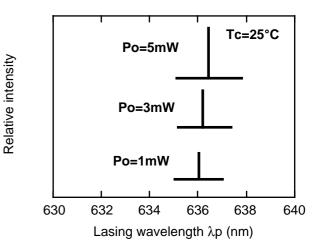
Lasing wavelength vs. Temperature



Beam divergence



Output power vs. Lasing wavelength





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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

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